

*B1*  
*C10*

a metal layer forming a plurality of top contact electrodes deposited on the p-doped wide energy gap semiconductor layer having patterned regions to confine current conduction in [desired] pixels of said EL device.

*B2*

3. (once amended) The EL device of claim 1, wherein said CNC layer [are] is selected from the group of semiconductor materials consisting of  $Zn_xCd_{1-x}Se$  (core) -  $Zn_yMg_{1-y}Se$  (cladding),  $Zn_xCd_{1-x}Se$  (core) -  $Zn_zBe_{1-z}Se$  (cladding),  $Zn_xCd_{1-x}Se$  (core) -  $ZnMgSSe$  (cladding),  $In_xGa_{1-x}N$  (core) - GaN (cladding), GaN (core)-AlGaN (cladding), and  $ZnCdS$  (core)-  $ZnMgS$  (cladding), where the subscripts x, y, z represent molar fractions.

*B3*

5. (once amended) The EL device of claim 1, wherein said CNC layer is sandwiched between lattice-matched wide energy gap semiconductor layers selected from the group of semiconductors consisting of  $Zn_aMg_{1-a}Se$ ,  $Zn_aMg_{1-a}S$ ,  $Zn_aMg_{1-a}S_bSe_{1-b}$ ,  $Zn_aBe_{1-a}S_bSe_{1-b}$ , Al<sub>c</sub>Ga<sub>1-c</sub>N, and AlInN, where the subscripts a, b and c represent molar fractions.

*B4*

6. (once amended) The EL device of claim 1, wherein said p-n junction is reverse-biased electrically to operate said device in the avalanche mode.

*B5*

7. (once amended) The EL device of claim 1, wherein said p-n junction is forward-biased electrically to operate in injection mode.

*B6*

8. (once amended) The EL device of claim 1, wherein the layer comprising CNC further comprises multiple sub-layers of differing CNCs sandwiched between epitaxially grown thin film layers of p- and n doped wide energy gap semiconductors.

*B7*

10. (once amended) The EL device as described in claim 1, wherein said CNC layer has more than one sublayer of differing CNCs stacked to emit different colors and white light .

*B8*

12.(once amended) The EL device as described in claim 1, wherein more than one said CNC layers are deposited to produce red, green and blue pixel elements for a display panel.

*B9*

44. (once amended) The EL device as described in claim 1 where the electrodes at the bottom of the device are separated by reverse biased junctions.--

#### REMARKS

The list of references has been deleted. Missing reference number in Fig.2(a) has been added. Typographical error in the specification has been corrected. Claims 1, 3, 5-8, 10, 12 and 44 have been amended.

The Examiner objected to the listing of references in the application. The list of references has been deleted.